#### TOSHIBA CMOS DIGITAL INTEGRATED CIRCUIT SILICON MONOLITHIC

# TC74VHC86F, TC74VHC86FN, TC74VHC86FS, TC74VHC86FT

## QUAD EXCLUSIVE OR GATE

The TC74VHC86 is an advanced high speed CMOS QUAD EXCLUSIVE OR GATE fabricated with silicon gate  $C^2MOS$  technology.

It achieves the high speed operation similar to equivalent Bipolar Schottky TTL while maintaining the CMOS low power dissipation.

The internal circuit is includes on output buffer, which provide high noise immunity and stable output.

An Input protection circuit ensures that 0 to 7V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5V to 3Vsystems and on two supply system such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

#### FEATURES:

- High Speed------t<sub>pd</sub> = 4.8ns(typ.) at  $V_{CC}$  = 5V
- Low Power Dissipation  $\dots I_{CC} = 2\mu A(Max.)$  at  $Ta = 25^{\circ}C$
- High Noise Immunity  $V_{\text{NIH}} = V_{\text{NIL}} = 28\% V_{\text{CC}}$  (Min.)
- Power Down Protection is provided on all inputs.
- Balanced Propagation Delays  $\cdots t_{pLH} \simeq t_{pHL}$
- Wide Operating Voltage Range  $W_{CC}$  (opr) = 2V ~ 5.5V
- Pin and Function Compatible with 74ALS86

#### **IEC LOGIC SYMBOL**







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#### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage Range	V <sub>cc</sub>	-0.5~7.0	V
DC Input Voltage	VIN	-0.5~7.0	V
DC Output Voltage	V <sub>OUT</sub>	-0.5~V <sub>CC</sub> +0.5	V
Input Diode Current	Ι <sub>ικ</sub>	- 20	mA
Output Diode Current	Ι <sub>οκ</sub>	± 20	mA
DC Output Current	I <sub>OUT</sub>	±25	mA
DC V <sub>cc</sub> /Ground Current	I <sub>cc</sub>	± 50	mA
Power Dissipation	P <sub>D</sub>	180	mW
Storage Temperature	T <sub>stg</sub>	-65~150	°C

#### **RECOMMENDED OPERATING CONDITIONS**

PARAMETER	SYMBOL	VALUE	UNIT
Supply Voltage	V <sub>cc</sub>	2.0~5.5	V
Input Voltage	VIN	0~5.5	V
Output Voltage	V <sub>OUT</sub>	0~V <sub>cc</sub>	V
Operating Temperature	T <sub>opr</sub>	- 40~85	°C
Input Rise and Fall Time	dt/dv	0~100 (V <sub>CC</sub> = 3.3 ± 0.3V) 0~20 (V <sub>CC</sub> = 5±0.5V)	ns / V

## DC ELECTRICAL CHARACTERISTICS

PARAMETER	SYMBOL			V <sub>cc</sub>	Т	Ta = 25°C			Ta = - 40~85°C	
			TEST CONDITION		MIN.	TYP.	MAX.	MIN.	MAX.	UNIT
High - Level				2.0	1.50	_	-	1.50	—	
Input Voltage	ViH	-		3.0~ 5.5	V <sub>cc</sub> × 0.7	—	—	$V_{cc} \times 0.7$	—	V
Low - Level				2.0 3.0~		—	0.50		0.50	
Input Voltage	Vil	-				—	V <sub>cc</sub> × 0.3	_	$V_{cc} \times 0.3$	V
	V <sub>OH</sub>		50.0	2.0	1.9	2.0	—	1.9	—	
Output Voltage V <sub>OH</sub>		V <sub>1 N</sub> =	I <sub>OH</sub> = — 50µА	3.0 4.5	2.9 4.4	3.0 4.5	_	2.9 4.4	_	V
	V <sub>IH</sub> or V <sub>IL</sub>	$I_{OH} = -4mA$ $I_{OH} = -8mA$	3.0 4.5	2.58 3.94	_	_	2.48 3.80	-		
		V <sub>1N</sub> =	<sub>N</sub> = Ι <sub>OL</sub> = 50μΑ			0.0 0.0	0.1 0.1	_	0.1 0.1	
Low - Level Output Voltage	Vol			3.0 4.5		0.0	0.1		0.1	V
		VIH or VIL	I <sub>OL</sub> = 4mA I <sub>OL</sub> = 8mA	3.0 4.5	_	_	0.36 0.36	=	0.44 0.44	
Input Leakage Current	I <sub>IN</sub>	$V_{IN} = 5.5 V \text{ or GND}$		0~5.5	Ι	_	±0.1	_	±1.0	
Quiescent Supply Current	I <sub>cc</sub>	$V_{IN} = V_{CC}$ or GND		5.5	_	—	2.0	_	20.0	μΑ

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AC ELECTRICAL CHARACTE	RISTICS ( I	nput  t <sub>r</sub> = t <sub>f</sub> = 3ns )	
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PARAMETER SYMBOL	CYMPOL	TEST CONDITION		-	Ta = 25°C	2	Ta = − 40~85°C			
	STIVIBUL	,OL	V <sub>cc</sub> (V)	CL (pF)	MIN.	TYP.	MAX.	MIN.	MAX.	
Propagation Delay Time	t <sub>pLH</sub> t <sub>pHL</sub>		3.3±0.3	15	—	7.0	11.0	1.0	13.0	ns
				50	—	9.5	14.5	1.0	16.5	
			5.0±0.5	15	—	4.8	6.8	1.0	8.0	
				50	—	6.3	8.8	1.0	10.0	
Input Capacitance	C <sub>IN</sub>				_	4	10	—	10	<b>_</b>
Power Dissipation Capacitance	<b>C</b> <sub>PD</sub>	(Note 1)			_	18	—	—	—	pF

Note (1)  $C_{PD}$  is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation :  $I_{CC(opr.)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC} / 4 \,(\,per \ Gate\,)$ 

# NOISE CHARACTERISTICS (Input $t_r = t_f = 3ns$ )

PARAMETER	SYMBOL	TEST CONDIT	Ta =	UNIT		
FARAIVIETER	STIVIBUL		V <sub>cc</sub> (V)	TYP.	LIMIT	
Quiet Output Maximum Dynamic V <sub>OL</sub>	V <sub>OLP</sub>	$C_L = 50 pF$	5.0	0.3	0.8	V
Quiet Output Minimum Dynamic V <sub>OL</sub>	V <sub>OLV</sub>	$C_L = 50 pF$	5.0	-0.3	-0.8	<
Minimum High Level Dynamic Input Voltage	V <sub>IHD</sub>	$C_L = 50 pF$	5.0		3.5	V
Maximum Low Level Dynamic Input Voltage	V <sub>ILD</sub>	$C_L = 50 pF$	5.0	_	1.5	v

## INPUT EQUIVALENT CIRCUIT





1997-01-30 4/5

## SSOP 14PIN OUTLINE DRAWING (SSOP14-P-225-0.65)



## TSSOP 14PIN OUTLINE DRAWING (TSSOP14-P-0044-0.65)



Unit in mm